

August 1998

100324

Low Power Hex TTL-to-ECL Translator

General Description

The 100324 is a hex translator, designed to convert TTL logic levels to 100K ECL logic levels. The inputs are compatible with standard or Schottky TTL. A common Enable (E), when LOW, holds all inverting outputs HIGH and holds all true outputs LOW. The differential outputs allow each circuit to be used as an inverting/non-inverting translator, or as a differential line driver. The output levels are voltage compensated over the full -4.2V to -5.7V range.

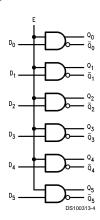
When the circuit is used in the differential mode, the 100324, due to its high common mode rejection, overcomes voltage gradients between the TTL and ECL ground systems. The $\rm V_{EE}$ and $\rm V_{TTL}$ power may be applied in either order.

The 100324 is pin and function compatible with the 100124 with similar AC performance, but features power dissipation roughly half of the 100124 to ease system cooling requirements.

Features

- Pin/function compatible with 100124
- Meets 100124 AC specifications
- 50% power reduction of the 100124
- Differential outputs
- 2000V ESD protection
- -4.2V to -5.7V operating range
- Standard Microcircuit Drawing (SMD) 5962-9153001

Logic Diagram

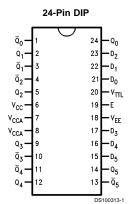


Pin Names	Description				
D ₀ -D ₅	Data Inputs				
E	Enable Input				
Q ₀ -Q ₅	Data Outputs				
Q_0-Q_5 $\overline{Q}_0-\overline{Q}_5$	Complementary				
	Data Outputs				

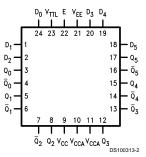
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DS100313

Connection Diagrams



24-Pin Quad Cerpak



Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Above which the useful life may be impaired.

Storage Temperature (T_{STG}) -65°C to +150°C

Maximum Junction Temperature (T_J)

+175°C Ceramic V_{EE} Pin Potential to Ground Pin -7.0V to +0.5V

 V_{TTL} Pin Potential to Ground Pin -0.5V to +6.0V Input Voltage (DC) -0.5V to +6.0V

Output Current (DC Output HIGH) -50 mA ESD (Note 2)

≥2000V

Recommended Operating Conditions

Case Temperature (T_C)

Military -55°C to +125°C -5.7V to -4.2V

Supply Voltage (V_{EE})

Note 1: Absolute maximum ratings are those values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: ESD testing conforms to MIL-STD-883, Method 3015.

Military Version

DC Electrical Characteristics

 V_{EE} = -4.2V to -5.7V, V_{CC} = V_{CCA} = GND, T_{C} = -55°C to +125°C, V_{TTL} = +4.5V to +5.5V

Parameter	Min	Max	Units	T _C	Conditi	Notes	
Output HIGH Voltage	-1025	-870	mV	0°C to +125°C	V _{IN} = V _{IH} (Max)	Loading with	(Notes 3, 4, 5)
	-1085	-870	mV	-55°C	or VIL (MIN)	50Ω to -2.0V	
Output LOW Voltage	-1830	-1620	mV	0°C to +125°C	1		
	-1830	-1555	mV	-55°C	1		
Output HIGH Voltage	-1035		mV	0°C to +125°C	V _{IN} = V _{IH} (Max)	Loading with	(Notes 3, 4, 5)
	-1085		mV	-55°C	or VIL (MIN)	50Ω to -2.0V	
Output LOW Voltage		-1610	mV	0°C to +125°C			
		-1555	mV	-55°C			
Input HIGH Voltage	2.0	5.0	V	-55°C to +125°C	Over V _{TTL} , V _{EE} , T _C Range		(Notes 3, 4, 5, 6)
Input LOW Voltage	0.0	0.8	V	-55°C to +125°C	Over V _{TTL} , V _{EE} , T _C Range		(Notes 3, 4, 5, 6)
Input HIGH Current		20	μA	-55°C to +125°C	V _{IN} = +2.7V		(Notes 3, 4, 5)
Breakdown Test		100	μA	-55°C to +125°C	V _{IN} = +7.0V		
Input LOW Current							
Data	-0.9		mA	-55°C to +125°C	V _{IN} = +0.4V		(Notes 3, 4, 5)
Enable	-5.4						
Input Clamp Diode Voltage		-1.2	V	-55°C to +125°C	- ""		(Notes 3, 4, 5)
VEE Power Supply Current	-70	-22	mA	-55°C to +125°C			(Notes 3, 4, 5)
V _{TTL} Power Supply Current 38 mA -55°C to +125°C All Inputs V _{IN} = GND				(Notes 3, 4, 5)			
	Output HIGH Voltage Output LOW Voltage Output HIGH Voltage Output LOW Voltage Input HIGH Voltage Input LOW Voltage Input HIGH Current Breakdown Test Input LOW Current Data Enable Input Clamp Diode Voltage VEE Power Supply Current	Output HIGH Voltage	Output HIGH Voltage -1025 -870 -1085 -870 Output LOW Voltage -1830 -1620 -1830 -1555 Output HIGH Voltage -1035 -1085 -1085 Output LOW Voltage -1610 Input HIGH Voltage 2.0 5.0 Input LOW Voltage 0.0 0.8 Input HIGH Current 20 5.0 Input HIGH Current 100 100 Input LOW Current -0.9 -5.4 Input Clamp Diode Voltage -1.2 VEE Power Supply Current -70 -22	Output HIGH Voltage -1025 -870 mV -1085 -870 mV Output LOW Voltage -1830 -1620 mV -1830 -1555 mV Output HIGH Voltage -1035 mV Output LOW Voltage -1610 mV Input HIGH Voltage 2.0 5.0 V Input LOW Voltage 0.0 0.8 V Input HIGH Current 20 μA Breakdown Test 100 μA Input LOW Current 0.9 mA Enable -5.4 -1.2 V VEE Power Supply Current -70 -22 mA	Output HIGH Voltage -1025 -870 mV 0°C to +125°C Output LOW Voltage -1830 -1620 mV 0°C to +125°C Output HIGH Voltage -1830 -1555 mV -55°C Output HIGH Voltage -1035 mV 0°C to +125°C -1085 mV -55°C Output LOW Voltage -1610 mV 0°C to +125°C Input HIGH Voltage 2.0 5.0 V -55°C Input LOW Voltage 0.0 0.8 V -55°C to +125°C Input HIGH Current 20 μA -55°C to +125°C Breakdown Test 100 μA -55°C to +125°C Input LOW Current 0.9 mA -55°C to +125°C Enable -5.4 -55°C to +125°C Input Clamp Diode Voltage -1.2 V -55°C to +125°C VEE Power Supply Current -70 -22 mA -55°C to +125°C	Output HIGH Voltage -1025 -870 mV 0°C to +125°C V _{IN} = V _{IH} (Max) or V _{IL} (Min) Output LOW Voltage -1830 -1620 mV 0°C to +125°C V _{IN} = V _{IH} (Max) or V _{IL} (Min) Output HIGH Voltage -1830 -1555 mV -55°C V _{IN} = V _{IH} (Max) or V _{IL} (Min) Output LOW Voltage -1035 mV 0°C to +125°C V _{IN} = V _{IH} (Max) or V _{IL} (Min) Output LOW Voltage -1610 mV 0°C to +125°C V _{IN} = V _{IH} (Max) or V _{IL} (Min) Input HIGH Voltage 2.0 5.0 V -55°C Over V _{TL} V _{EE} , T _C F Input HIGH Current 2.0 5.0 V -55°C to +125°C Over V _{TTL} , V _{EE} , T _C F Breakdown Test 100 μA -55°C to +125°C V _{IN} = +7.0V Input LOW Current Data -0.9 mA -55°C to +125°C V _{IN} = +0.4V Enable -5.4 -1.2 V -55°C to +125°C All Inputs V _{IN} = +4.0V	Output HIGH Voltage −1025 −870 mV 0°C to +125°C VI _{IN} = V _{IH} (Max) or VIL (Min) Loading with 50Ω to −2.0V Output LOW Voltage −1830 −1620 mV 0°C to +125°C VI _{IN} = V _{IH} (Max) or VIL (Min) Loading with 50Ω to −2.0V Output HIGH Voltage −1035 mV −55°C VI _{IN} = V _{IH} (Max) or VIL (Min) Loading with 50Ω to −2.0V Output LOW Voltage −1610 mV −55°C VI _{IN} = V _{IH} (Max) or VIL (Min) Loading with 50Ω to −2.0V Input HIGH Voltage −1610 mV −55°C VIII = VIH (Max) or VIL (Min) Loading with 50Ω to −2.0V Input HIGH Voltage −1610 mV −55°C VIII = VIH (Max) or VIL (Min) Loading with 50Ω to −2.0V Input HIGH Voltage −0.0 N −55°C Over VTTL VEE, To Range Input HIGH Voltage 0.0 0.8 V −55°C to +125°C Over VTTL, VEE, To Range Input LOW Current 20 µA −55°C to +125°C VIN = +2.7V Brable −5.4 mA −55°C to +125°C VIN = +0.4V Input Clamp Diode Volt

Note 3: F100K 300 Series cold temperature testing is performed by temperature soaking (to guarantee junction temperature equals -55°C), then testing immediately without allowing for the junction temperature to stabilize due to heat dissipation after power-up. This provides "cold start" specs which can be considered a worst case condition at cold temperatures.

Note 4: Screen tested 100% on each device at -55°C, +25°C, and +125°C, Subgroups 1, 2, 3, 7, and 8.

Note 5: Sample tested (Method 5005, Table I) on each manufactured lot at -55°C, +25°C, and +125°C, Subgroups A1, 2, 3, 7, and 8.

Note 6: Guaranteed by applying specified input condition and testing V_{OH}/V_{OL}

AC Electrical Characteristics

 $V_{\rm EE}$ = -4.2V to -5.7V, $V_{\rm CC}$ = $V_{\rm CCA}$ = GND, $V_{\rm TTL}$ = +4.5V to +5.5V

Symbol	Parameter	T _C =	–55°C	T _C = +25°C		T _C = +125°C		Units	Conditions	Notes
		Min	Max	Min	Max	Min	Max			
tpLH	Propagation Delay	0.50	3.00	0.50	2.90	0.30	3.30	ns		(Notes 7, 8, 9)
tpHL	Data and Enable to Output								Figures 1, 2	
tTLH	Transition Time	0.35	1.80	0.45	1.80	0.45	1.80	ns		(Note 10)
tTHL	20% to 80%, 80% to 20%									

Note 7: F100K 300 Series cold temperature testing is performed by temperature soaking (to guarantee junction temperature equals –55°C), then testing immediately after power-up. This provides "cold start" specs which can be considered a worst case condition at cold temperatures

Note 8: Screen tested 100% on each device at +25°C temperature only, Subgroup A9.

Note 9: Sample tested (Method 5005, Table I) on each manufactured lot at +25°C, Subgroup A9, and at +125°C and -55°C temperatures, Subgroups A10 and A11.

Note 10: Not tested at +25°C, +125°C, and -55°C temperature (design characterization data).

Switching Waveform

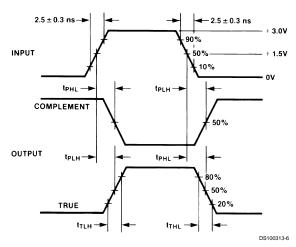
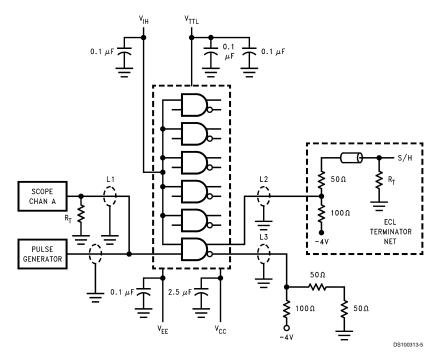


FIGURE 1. Propagation Delay and Transition Times

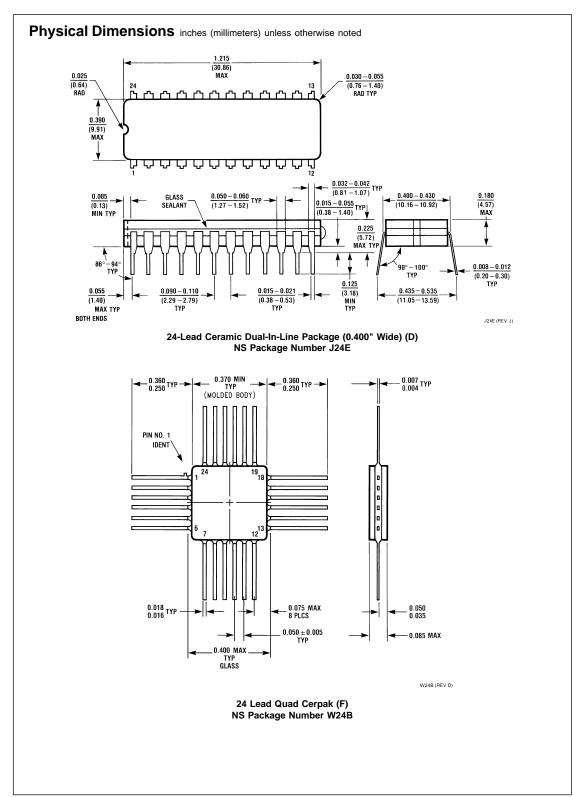
Test Circuit



Note: $V_{CC}, V_{CCA} = 0V, V_{EE} = -4.5V, V_{TL} = +5.0V, V_{IH} = +3.0V$ L1, L2 and L3 = equal length 50Ω impedance lines $R_T = 50\Omega \text{ terminator internal to scope}$ Decoupling 0.1 μ F from GND to V_{CC}, V_{EE} and V_{TL} All unused outputs are loaded with 50Ω to -2V or with equivalent ECL terminator network

C_L = Fixture and stray capacitance ≤ 3 pF

FIGURE 2. AC Test Circuit



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